

SEMITOP® 3

IGBT Module

SK30GD066ET

Target Data

Features

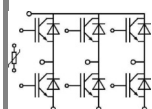
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

- Inverter up to 10 kVA
- Typ. motor power 4 kW

Remarks

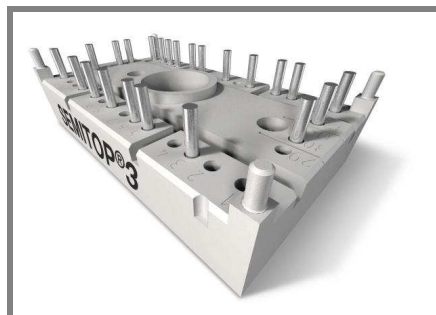
- $V_{isol} = 3000V$ AC, 50Hz, 1s



GD-ET

Absolute Maximum Ratings				$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions			Values	Units
IGBT					
V_{CES}	$T_j = 25\text{ °C}$			600	V
I_C	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$		40	A
		$T_s = 70\text{ °C}$		31	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$			60	A
V_{GES}				± 20	V
t_{psc}	$V_{CC} = 360\text{ V}$; $V_{GE} \leq 20\text{ V}$; $T_j = 150\text{ °C}$ $V_{CES} < 600\text{ V}$			6	μs
Inverse Diode					
I_F	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$		36	A
		$T_s = 70\text{ °C}$		28	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$			60	A
I_{FSM}	$t_p = 10\text{ ms}$; half sine wave $T_j = 150\text{ °C}$			160	A
Module					
$I_{t(RMS)}$					A
T_{vj}				-40 ... +175	$^{\circ}C$
T_{stg}				-40 ... +125	$^{\circ}C$
V_{isol}	AC, 1 min.			2500	V

Characteristics			T _s = 25 °C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 0,43 mA		5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES}	T _J = 25 °C T _J = 125 °C	0,0016			mA mA
I _{GES}	V _{CE} = 0 V, V _{GE} = 20 V	T _J = 25 °C T _J = 125 °C	300			nA nA
V _{CE0}		T _J = 25 °C T _J = 150 °C		0,9 0,8	1,1 1	V V
r _{CE}	V _{GE} = 15 V	T _J = 25°C T _J = 150°C		18,3 28	25 35	mΩ mΩ
V _{CE(sat)}	I _{Cnom} = 30 A, V _{GE} = 15 V	T _J = 25°C _{chiplev.} T _J = 125°C _{chiplev.}		1,45 1,65	1,85 2,05	V V
C _{ies} C _{oes} C _{res}	V _{CE} = 25, V _{GE} = 0 V	f = 1 MHz		1,63 0,11 0,05		nF nF nF
Q _G	V _{GE} =-7V...+15V			275		nC
t _{d(on)} t _r E _{on}	R _{Gon} = 25 Ω di/dt = 2335 A/μs	V _{CC} = 300V I _C = 30A		24 27 0,97		ns ns mJ
t _{d(off)} t _f E _{off}	R _{Goff} = 25 Ω di/dt = 2335 A/μs	T _J = 150 °C V _{GE} =-7/+15V		328 54 1,77		ns ns mJ
R _{th(j-s)}	per IGBT			1,65		K/W



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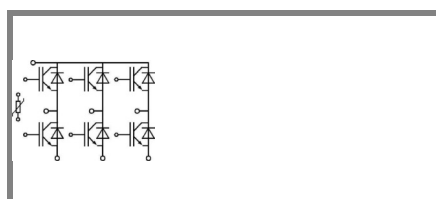
Remarks

- $V_{isol} = 3000V$ AC, 50Hz, 1s

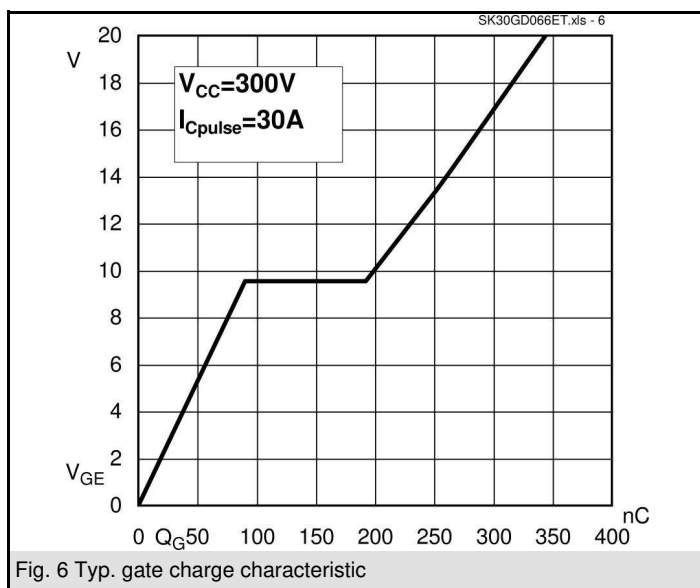
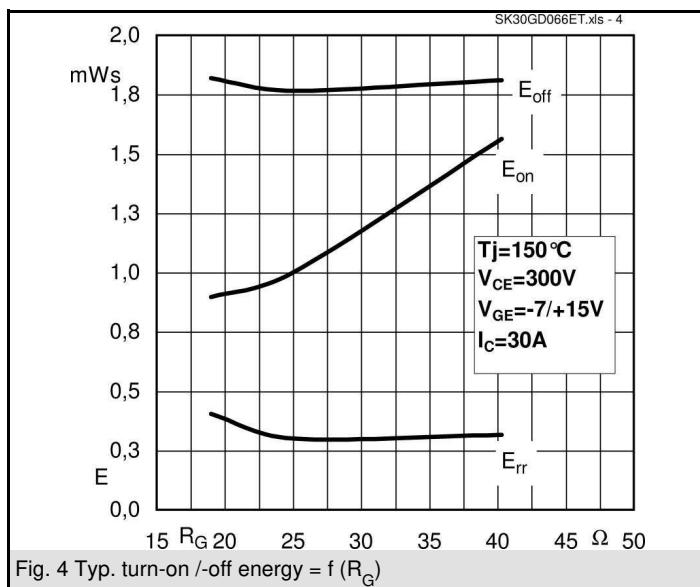
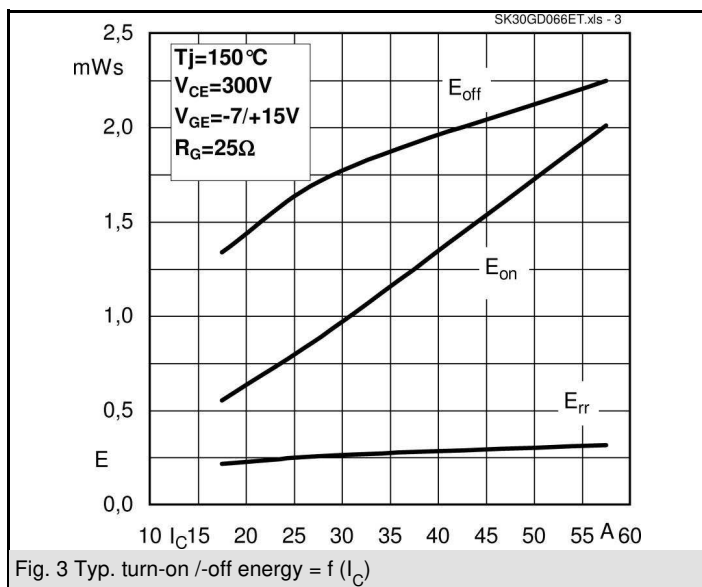
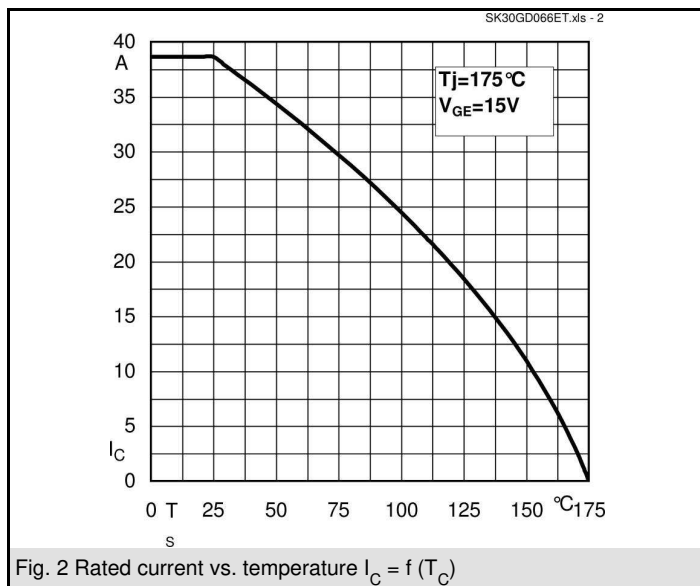
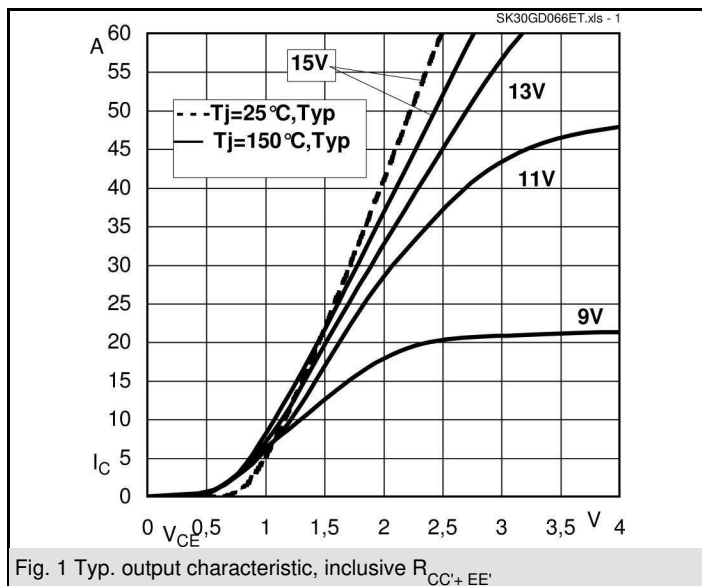
Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 30 A$; $V_{GE} = 0 V$				
	$T_j = 25 ^\circ C_{chiplev.}$		1,45	1,7	V
	$T_j = 150 ^\circ C_{chiplev.}$		1,45	1,7	V
V_{F0}					
	$T_j = 25 ^\circ C$		1	1,1	V
	$T_j = 150 ^\circ C$		0,9	1	V
r_F					
	$T_j = 25 ^\circ C$		15	20	mΩ
	$T_j = 150 ^\circ C$		18	23,3	mΩ
I_{RRM}	$I_F = 30 A$		30		A
Q_{rr}	$di/dt = 2335 A/\mu s$		1,6		μC
E_{rr}	$V_{CC} = 300V$		0,26		mJ
$R_{th(j-s)D}$	per diode		2,1		K/W
M_s	to heat sink	2,25		2,5	Nm
w			30		g
Temperature sensor					
R_{100}	$T_s = 100^\circ C$ ($R_{25} = 5k\Omega$)		493±5%		Ω

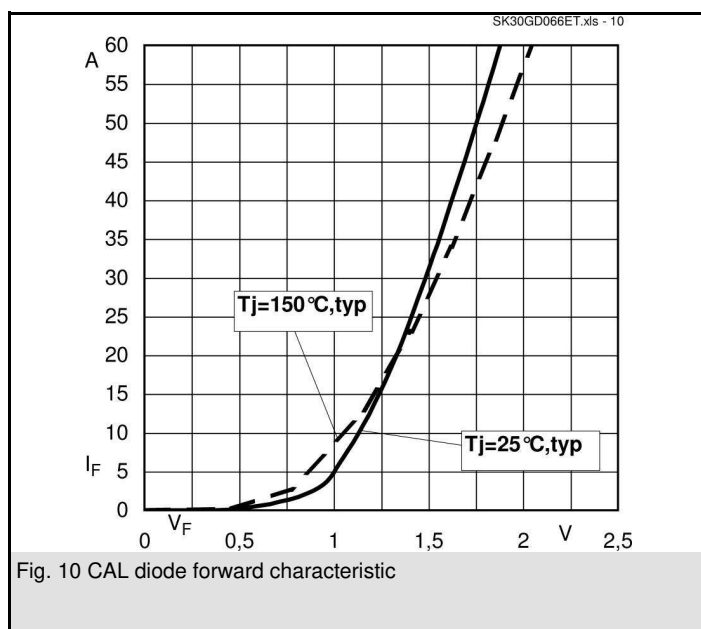
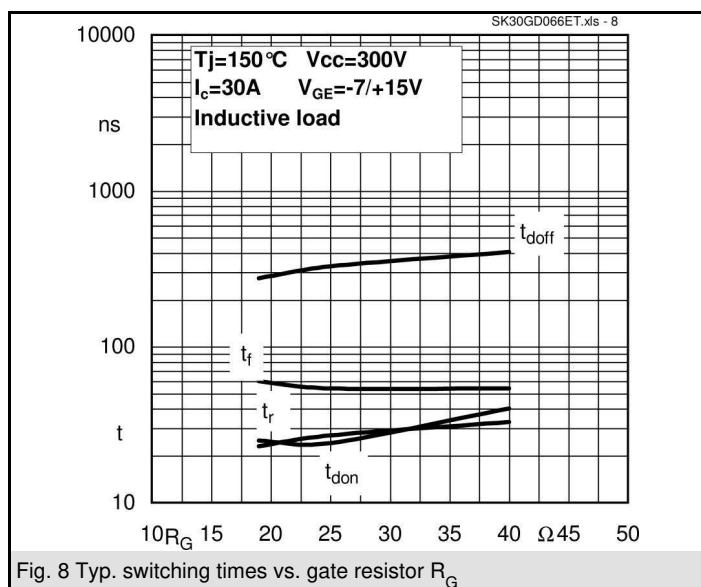
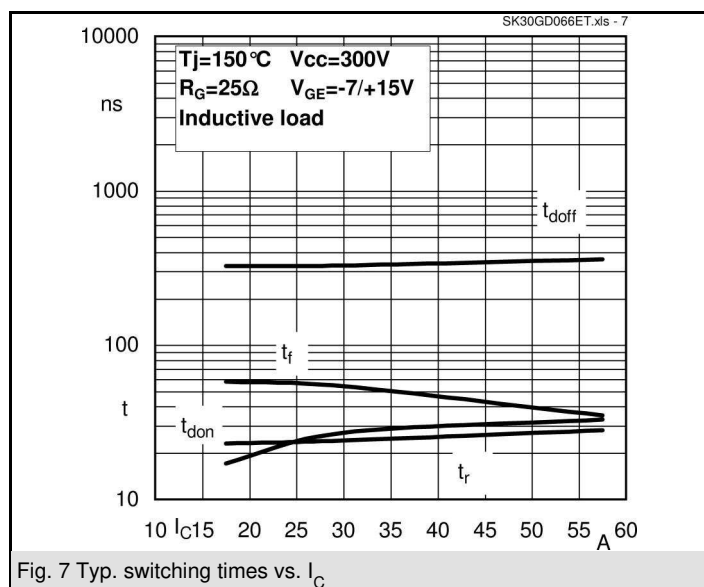
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

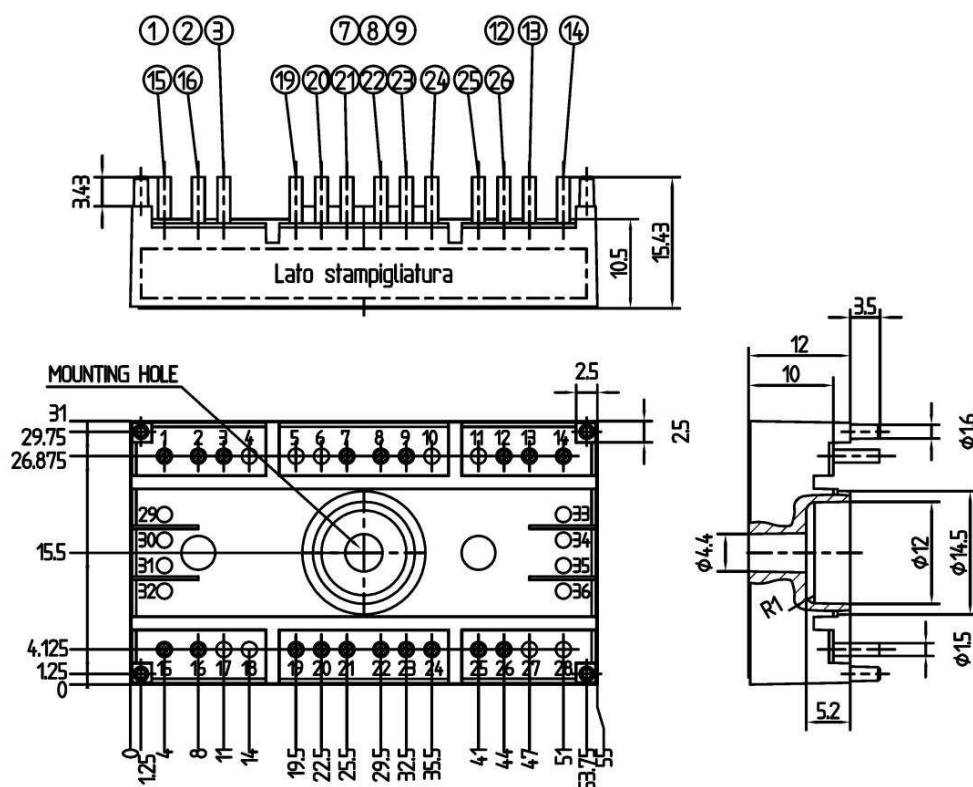
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



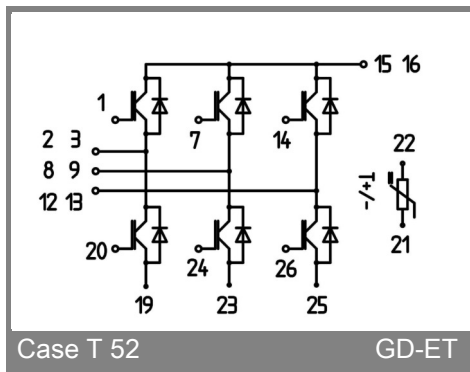
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Case T52 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 52

GD-ET